## TOSHIBA Photocoupler GaAs Ired & Photo-Triac

# **TLP361J**

Triac Drivers
Programmable Controllers
AC-Output Modules
Solid State Relays

The TOSHIBA TLP361J consists of a zero-voltage-crossing turn-on photo-triac optically coupled to a gallium arsenide infrared-emitting diode in a four-lead plastic DIP package.

• Peak off-state voltage: 600 V (Min.)

• Trigger LED current: 10 mA (Max.)

· On-state current: 100 mA (Max.)

• Isolation voltage: 5000 Vrms (Min.)

· Zero crossing Function

• UL recognized: UL1577, file No. E67349

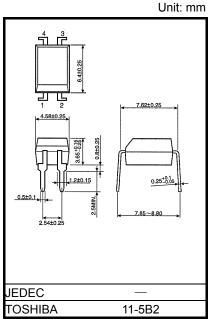
·Option (D4) type

TÜV approved: DIN EN60747-5-2

Certificate No. R50033433

Maximum operating insulation voltage : 890 Vpk Maximum permissible overvoltage : 8000 Vpk

(Note) When an EN60747-5-2 approved type is needed, please designate "Option (D4)."



Weight: 0.26 g (Typ.)

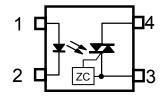
#### Construction mechanical rating

	7.62 mm pitch TLPXXX type	10.16 mm pitch TLPXXX type
Creepage distance	7.0 mm (min)	8.0 mm (min)
Clearance Insulation thickness	7.0 mm (min) 0.4 mm (min)	8.0 mm (min) 0.4 mm (min)

### •Trigger LED current

Classi-	Trigger LED V⊤=3V.	Marking of	
fication*	Min.	Max.	classification
(IFT7)		7	T7
Standard	1	10	T7、blank

## Pin Configuration (top view)



1: Anode

2: Cathode

3: Terminal1

4: Terminal2

(Note) When specifying the application type name for certification testing, be sure to use the standard product type name, e.g., TLP361J(IFT7): TLP361J

<sup>\*</sup>Example: "(IFT7)"; "TLP361J(IFT7)"

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic				Rating	Unit	
Forward current				50	mA	
	Forward current derating (Ta ≥ 53°C)		ΔI <sub>F</sub> /°C	-0.7	mA /°C	
ED	Peak forward current (100 µs pulse, 100 pps)		I <sub>FP</sub>	1	Α	
	Reverse voltage		V <sub>R</sub>	5	V	
	Junction temperature		Tj	125	°C	
Off-state output terminal voltage				600	V	
On-state RMS current	On-state RMS current	Ta = 25°C	I <sub>T(RMS)</sub>	100	mA	
	on-state Kino current	Ta = 70°C	TI(KIVIS)	50		
Detector	On-state current derating (Ta ≥ 25°C)	ΔI <sub>T</sub> /°C	-1.1	mA /°C		
Δ	Peak on-state current (100 µs pulse, 120 pps)		I <sub>TP</sub>	2	Α	
	Peak nonrepetitive surge current (Pw = 10 ms, DC =	10%)	I <sub>TSM</sub>	1.2	Α	
	Junction temperature	Tj	115	°C		
Stor	rage temperature range	T <sub>stg</sub>	-55~125	°C		
Operating temperature range			T <sub>opr</sub>	-40~100	°C	
Lead soldering temperature (10s)			T <sub>sol</sub>	260	°C	
Isola	Isolation voltage (AC, 1 min., R.H.≤ 60%) (Note 1)			5000	Vrms	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.

**Recommended Operating Conditions** 

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V <sub>AC</sub>	_	_	240	V <sub>ac</sub>
Forward current	lF	15	20	25	mA
Peak on-state current	I <sub>TP</sub>	_	_	1	Α
Operating temperature	T <sub>opr</sub>	-25	_	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

# **Electrical Characteristics (Ta = 25°C)**

	Characteristic	Symbol	Test Condition		Тур.	Max.	Unit
	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA		1.15	1.3	V
LED	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μA
	Capacitance	C <sub>T</sub>	V = 0, f = 1 MHz	_	30	_	pF
	Peak off-state current	I <sub>DRM</sub>	V <sub>DRM</sub> = 600 V	_	10	1000	nA
L	Peak on-state voltage	V <sub>TM</sub>	I <sub>TM</sub> = 100 mA	_	1.7	3.0	V
Detector	Holding current	lΗ	_	_	0.6	_	mA
Det	Critical rate of rise of off-state voltage	dv/dt	Vin = 240 Vrms , Ta = 85°C (Note 2)	200	500	_	V/µs
	Critical rate of rise of commutating voltage	dv/dt(c)	Vin = 60 Vrms , I <sub>T</sub> = 1 5mA (Note 2)	_	0.2		V/µs

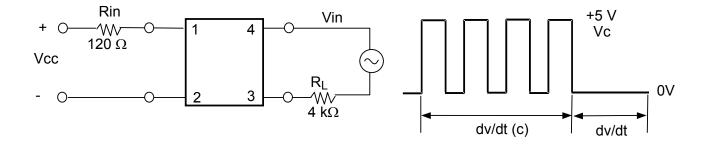
**Coupled Electrical Characteristics (Ta = 25°C)** 

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I <sub>FT</sub>	V <sub>T</sub> = 3 V	_	_	10	mA
Inhibit voltage	V <sub>IH</sub>	I <sub>F</sub> = Rated I <sub>FT</sub>	_	_	20	V
Leakage in inhibited state	l <sub>IH</sub>	I <sub>F</sub> = Rated I <sub>FT</sub>	ı	200	600	μA
		V <sub>T</sub> = Rated V <sub>DRM</sub>				
Turn-on time	t <sub>ON</sub>	$V_D = 3 \rightarrow 1.5 \text{ V}$ , $R_L = 20 \Omega$	_	30	100	μs
		I <sub>F</sub> = Rated I <sub>FT</sub> X1.5				

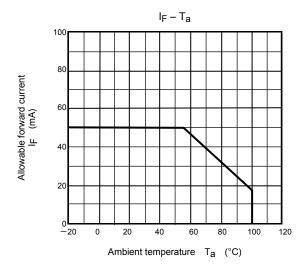
# **Isolation Characteristics (Ta = 25°C)**

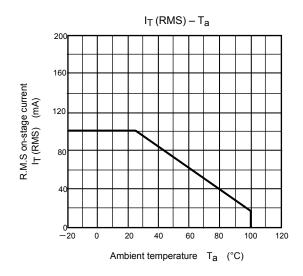
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	CS	V <sub>S</sub> = 0 , f = 1 MHz	_	8.0	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage	$BV_S$	AC, 1 minute	5000		_	Vrms
		AC, 1 second, in oil	_	10000	_	VIIIIS
		DC, 1 minute, in oil	_	10000		Vdc

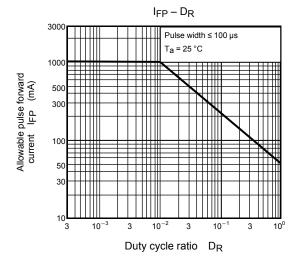
(Note 2): dv/dt test circuit

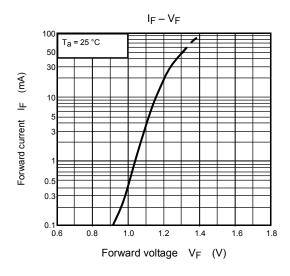


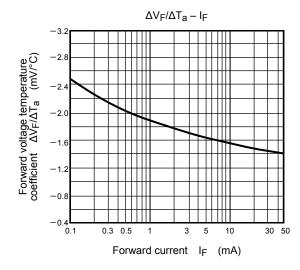
3

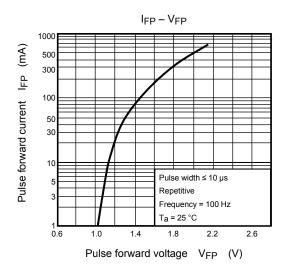




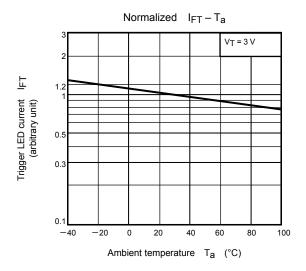


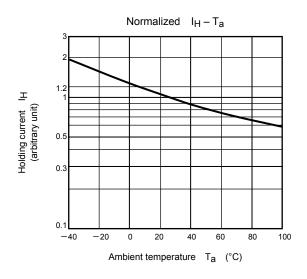


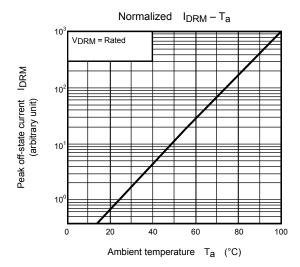


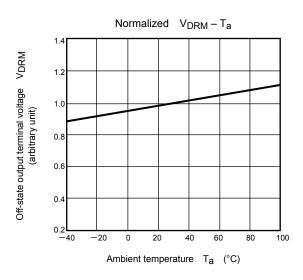


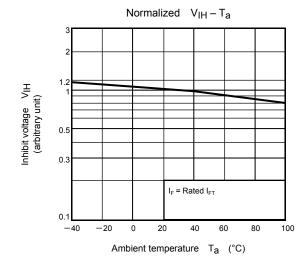
<sup>\*:</sup> The above graphs show typical characteristics.

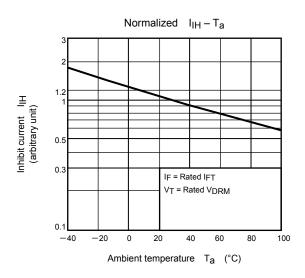












<sup>\*:</sup> The above graphs show typical characteristics.

#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
  In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in his document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No
  responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which
  may result from its use. No license is granted by implication or otherwise under any patents or other rights of
  TOSHIBA or the third parties.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.
- Please contact your sales representative for product-by-product details in this document regarding RoHS
  compatibility. Please use these products in this document in compliance with all applicable laws and regulations
  that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses
  occurring as a result of noncompliance with applicable laws and regulations.